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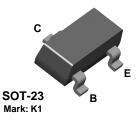
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BCW71



NPN General Purpose Amplifier

This device is designed for general purpose amplifier applications at collector currents to 300 mA. Sourced from Process 10.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	45	V
V _{CES}	Collector-Base Voltage	50	V
V _{EBO}	Emitter-Base Voltage	5.0	V
lc	Collector Current - Continuous	500	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах	Units
		*BCW71	
PD	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/°C
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

*Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

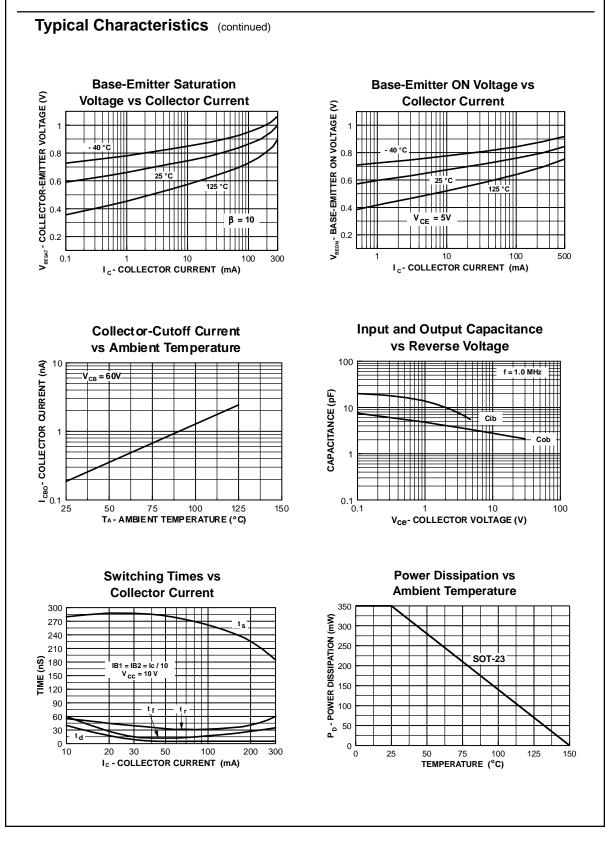
NPN General Purpose Amplifier (continued)

Symbol	Parameter Test Conditions		Min	Тур	Мах	Units
	RACTERISTICS					
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$	45			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{C} = 10 \ \mu A, I_{E} = 0$	50			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \ \mu {\rm A}, \ I_{\rm C} = 0$	5.0			V
I _{CBO}	Collector-Cutoff Current	$V_{CB} = 20 \text{ V}, I_E = 0$ $V_{CB} = 20 \text{ V}, I_E = 0, T_A = 100^{\circ}\text{C}$			100 10	μA
			- -			
	ACTERISTICS IDC Current Gain	I _C = 2.0 mA, V _{CE} = 5.0 V	110		220	
h _{FE}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 2.0 \text{ mA}, V_{\rm CE} = 5.0 \text{ v}$ $I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$	110		0.25	V
V _{CE(sat)}	Base-Emitter Saturation Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$ $I_{\rm C} = 50 \text{ mA}, I_{\rm B} = 2.5 \text{ mA}$	<u> </u>	0.85	0.25	V
V _{BE(sat)}	_		0.6	0.65	0.75	-
V _{BE(on)}	Base-Emitter On Voltage	$I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$	0.6		0.75	V
SMALL SI	GNAL CHARACTERISTICS Current Gain - Bandwidth Product	$I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ f = 35 MHz		330		MHz
Cobo	Output Capacitance	$V_{CE} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$			4.0	pF
Cibo	Input Capacitance	$V_{EB} = 0.5 \text{ V}, I_{C} = 0, f = 1.0 \text{ MHz}$		9.0		pF
NF	Noise Figure	$I_C = 0.2 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $R_S = 2.0 \text{ k}\Omega, f = 1.0 \text{ kHz},$ BW = 200 Hz			10	dB
Туріса	al Characteristics					
	Typical Pulsed Current Gain	Collector-E	Emitter	· Satura	ation	
NI 400	Typical Pulsed Current Gain vs Collector Current	Collector-E ହି Voltage vs				

BCW71

BCW71

NPN General Purpose Amplifier (continued)



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Datasheet Identification	Product Status	Definition
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